

FIG. 1

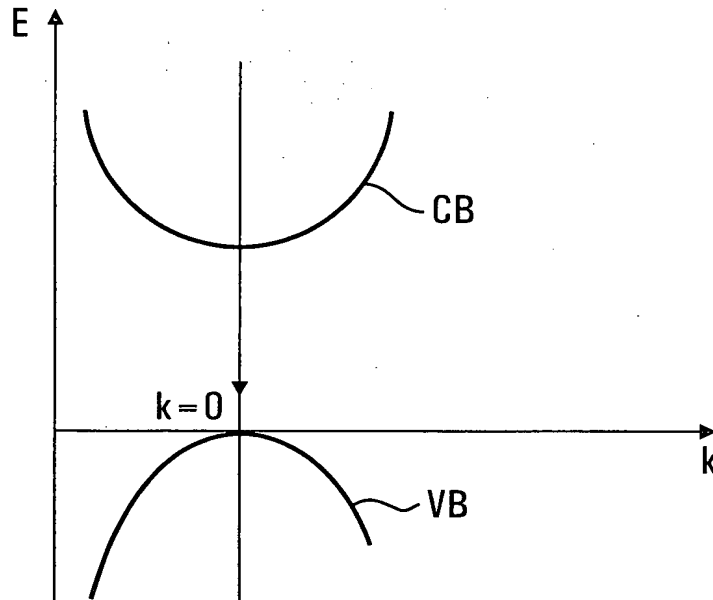


FIG. 2

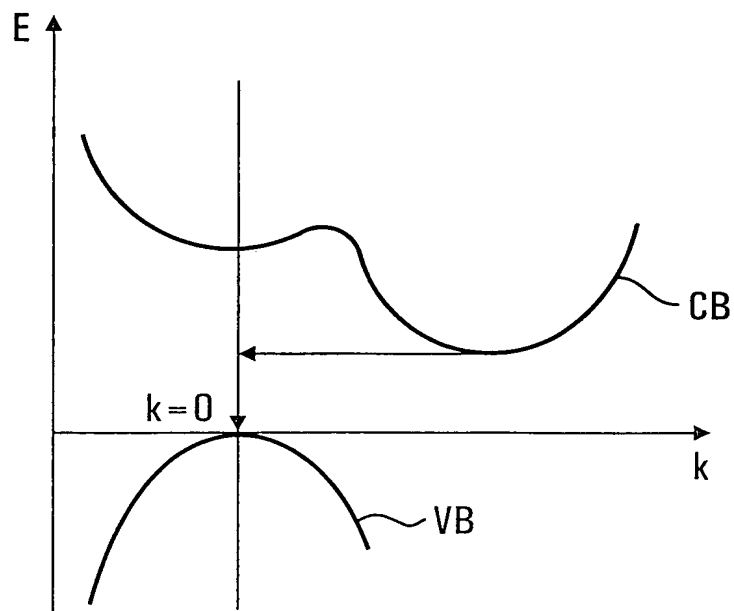


FIG. 3

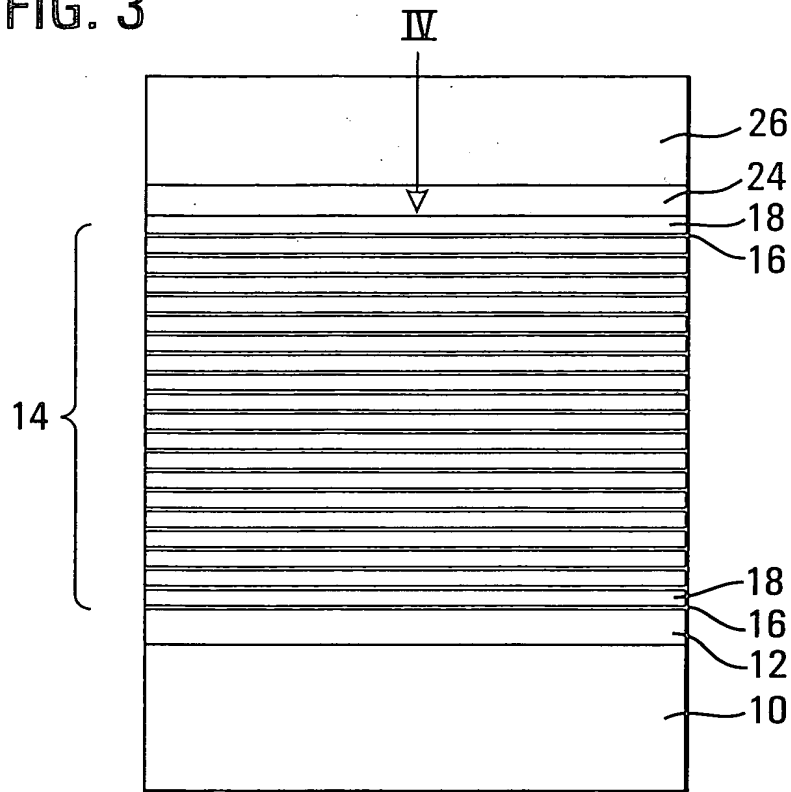


FIG. 4

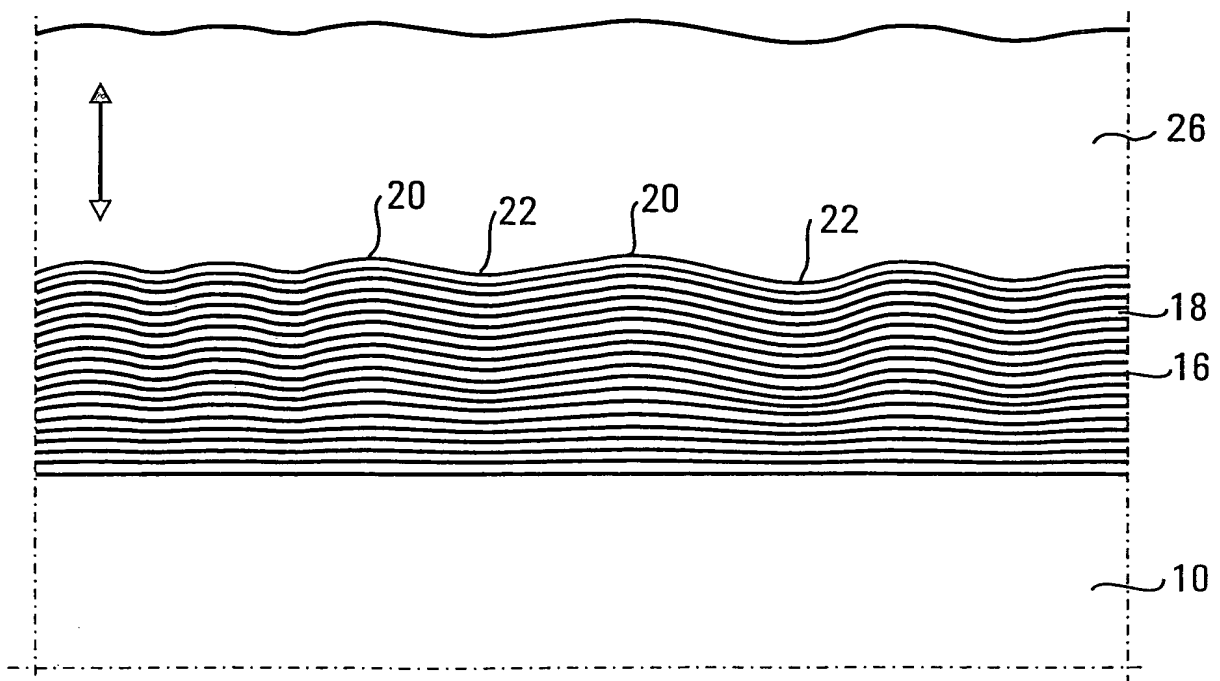


FIG. 5

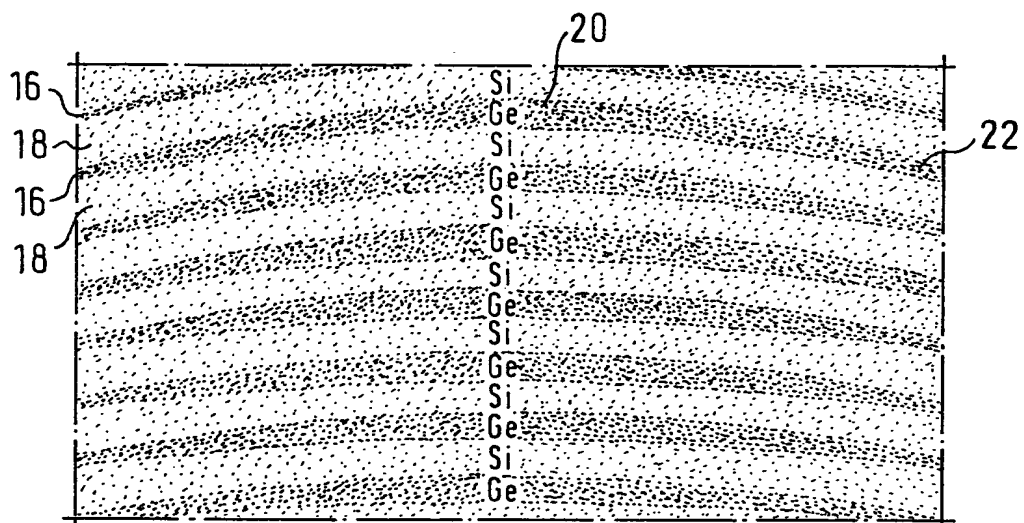


FIG. 6

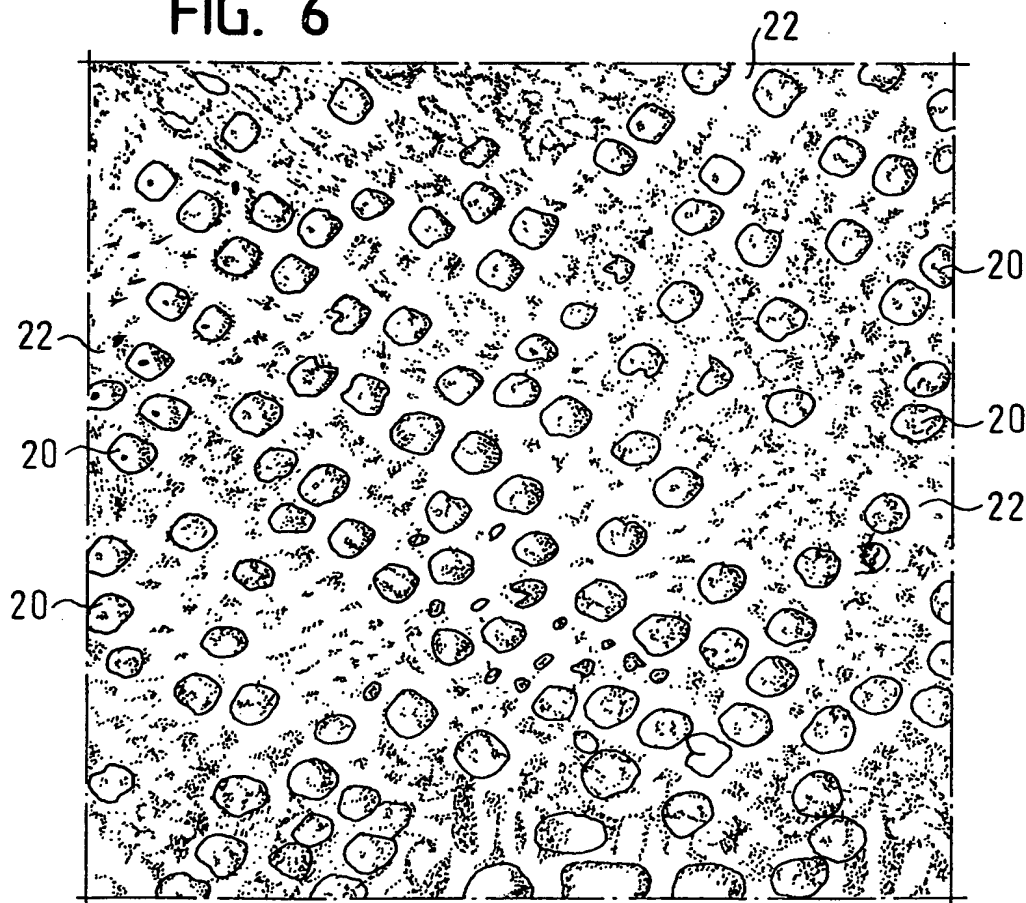


FIG. 7

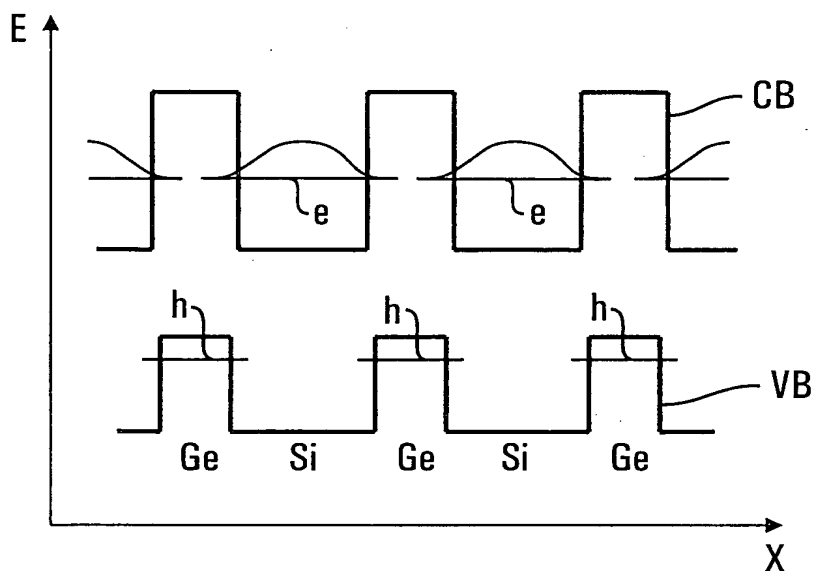
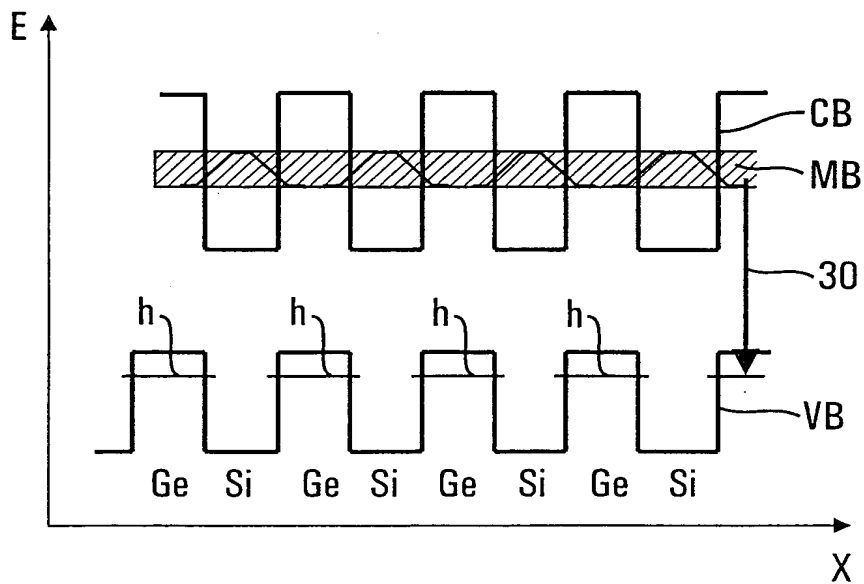


FIG. 8



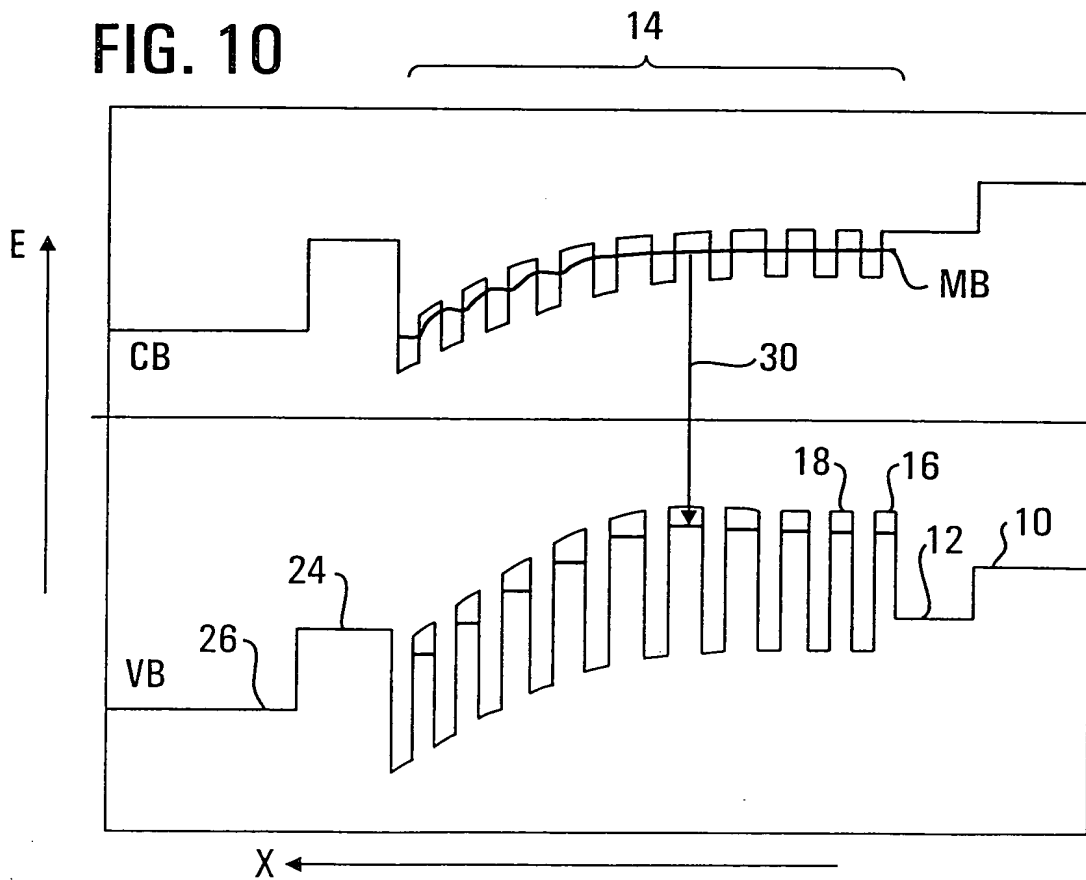
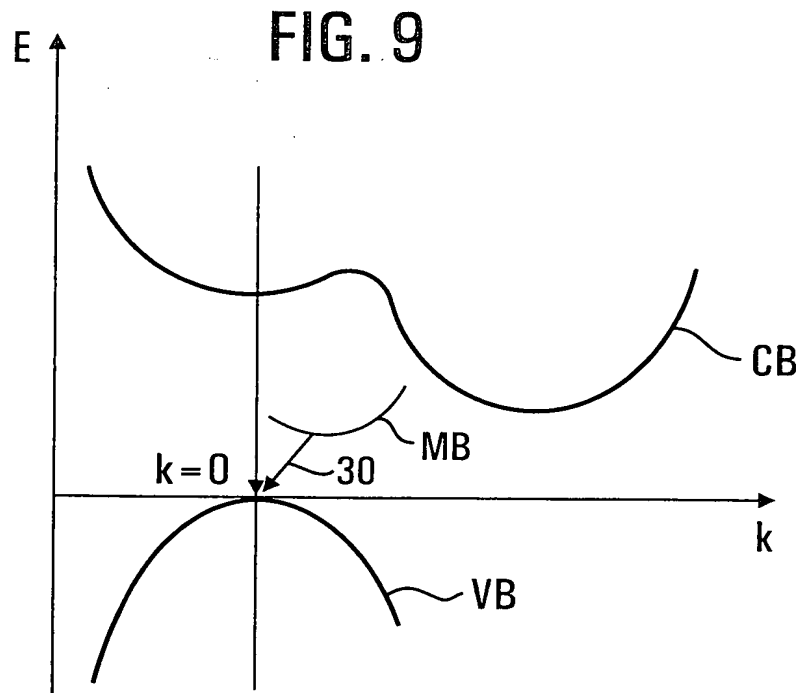


FIG. 11

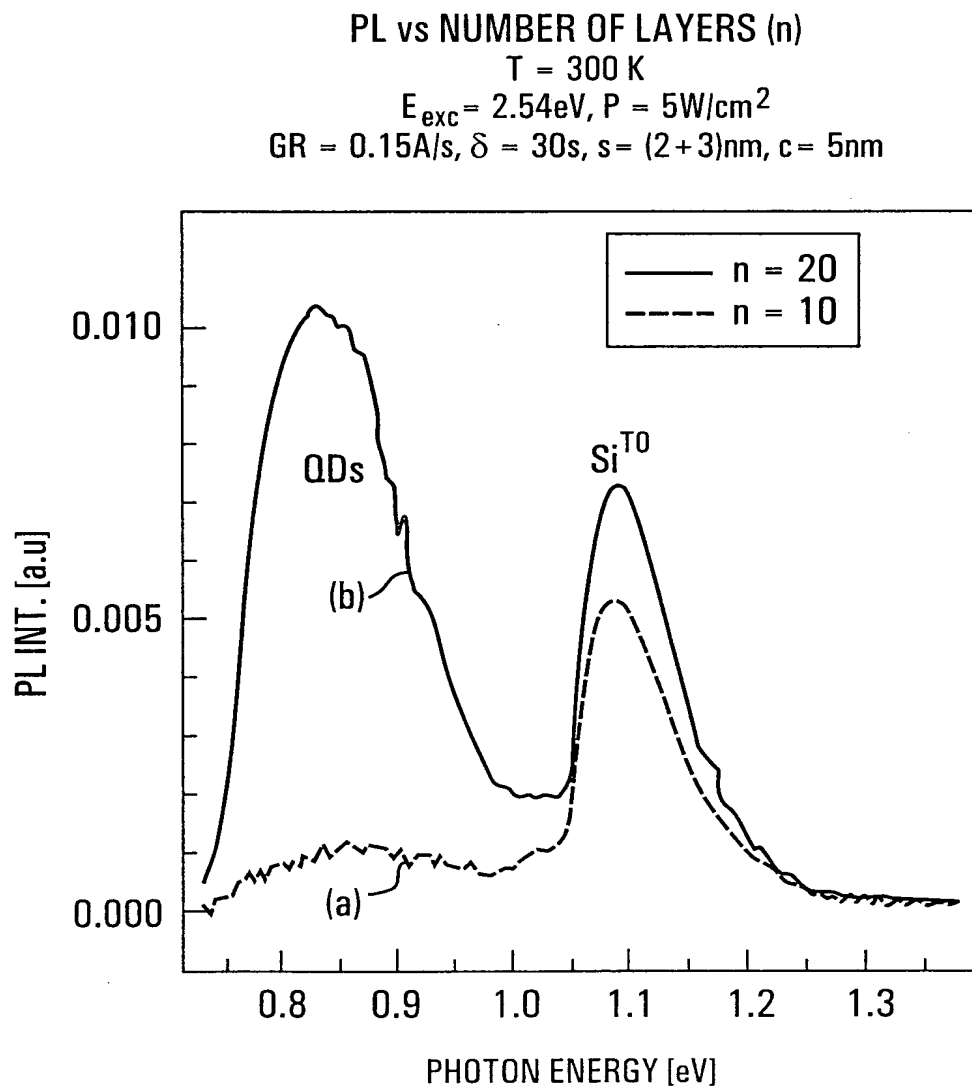


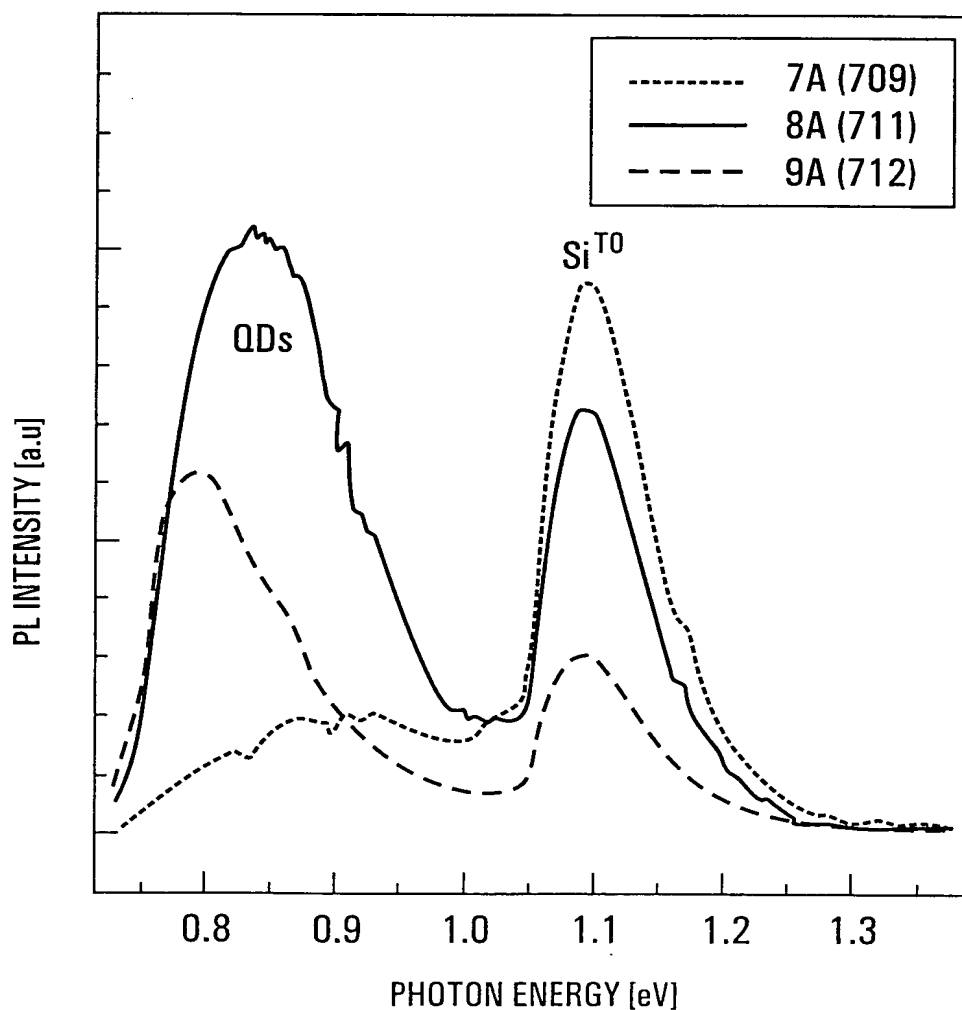
FIG. 12

PL vs Ge THICKNESS (d)

T = 300K

$E_{exc} = 2.54\text{eV}$ ,  $P = 5\text{W/cm}^2$

GR = 0.15A/s, c = 5nm



## FIG. 13

Ge-QDs vs InAs-QDs [LTLS]

PL at T = 300K

$E_{\text{exc}} = 2.54\text{eV}$ ,  $P = 1\text{W}/\text{cm}^2$

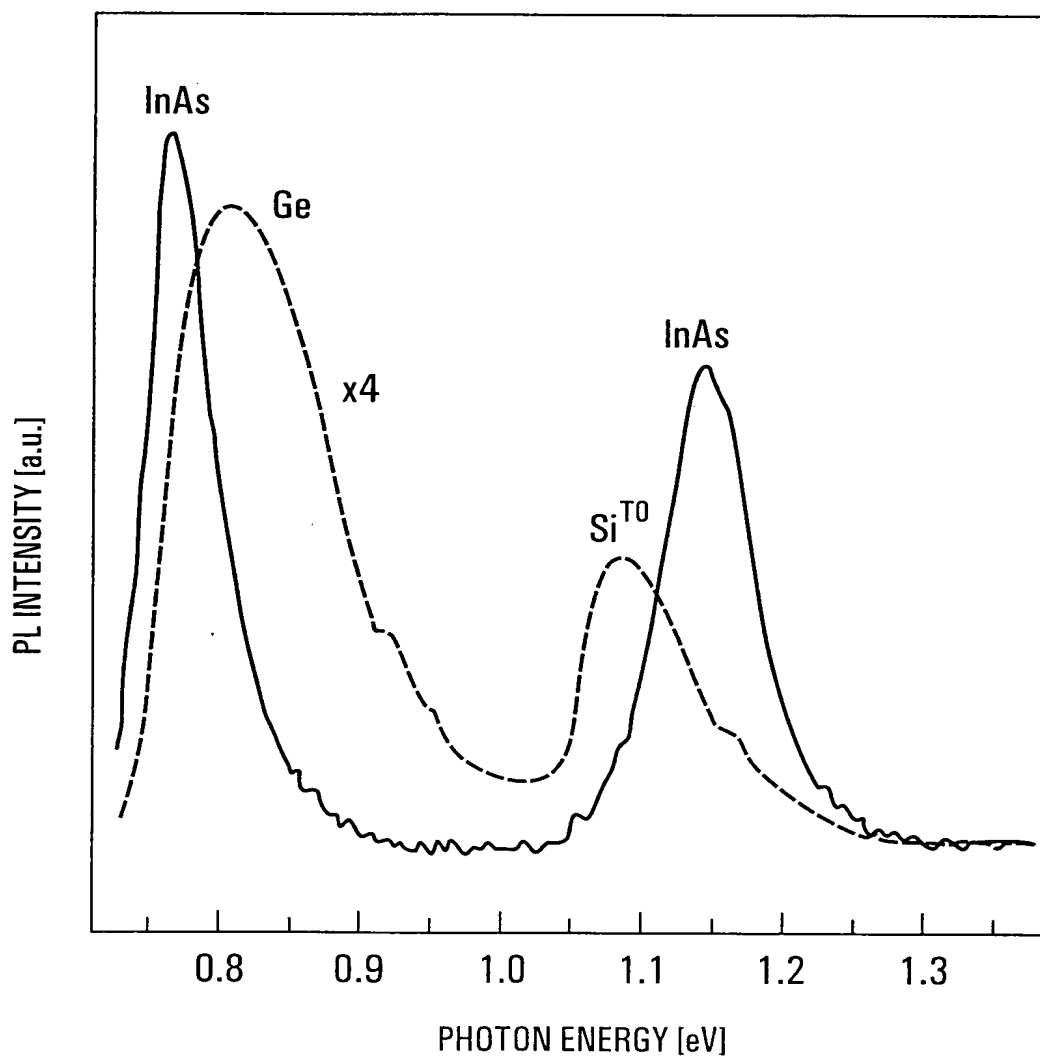




FIG. 14

